LISTING of CLAIMS

1-12. (Cancelled)

13. (Currently amended) A process for selectively removing silicon dioxide and photoresist sidewall residue after ~~drywall~~ dry etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution consisting essentially of;

(a) sulfuric acid,

(b) hydrogen fluoride ~~hydrofluoric acid~~, ammonium fluoride or an alkali metal fluoride,

and

(c) hydrogen peroxide,

wherein said solution contacts said sidewall residue effectively to remove it from said dry etched wafer,

and wherein the ratio (a):(b) is in the range of from 10:1 to 700:1 by weight.

14. (Previously presented) A process for removing photoresist according to claim 13, wherein the photoresist is effective for g-line, i-line, deep UV, E-beam or X-ray.

15. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.

16. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for about 10 minutes.

17. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at about 1 atm.

18. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.

19. (Previously presented) A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of from 120 to 140 degrees C.

20. (Currently amended) A process for removing photoresist after ~~drywall~~ dry etching according to claim 13, wherein ~~the fluorine-containing compound~~ (b) is ~~hydrofluoric acid~~ hydrogen fluoride.

21. (Currently amended) A process for selectively removing silicon dioxide and photoresist after ~~drywall~~ dry etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution consisting essentially of sulfuric acid, hydrofluoric acid and hydrogen peroxide ~~according to claim 20,~~ wherein the ratio of sulfuric acid ~~to~~ plus hydrofluoric acid ~~and~~ to hydrogen peroxide is 3:1 by volume.

22. (Cancel)

23. (Cancel)

24 (New) A process for removing photoresist after dry etching according to claim 13, wherein the ratio (a):(b) is in the range of from 100:1 to 700:1 by weight.

25. (New) A process for removing photoresist after dry etching according to claim 13, wherein the ratio (a):(b) is in the range of from 300:1 to 500:1 by weight.

26. (New) A process for removing photoresist after dry etching according to claim 13, wherein the ratio of sulfuric acid plus ammonium fluoride to hydrogen peroxide is 3:1 by volume.

27. (New) A process for removing photoresist after dry etching according to claim 13, wherein (b) is ammonium fluoride or an alkali metal fluoride.